STGB10NC60K

10 A, 600 V short-circuit rugged IGBT

Features

- Low on voltage drop (V_{CESAT})
- Short-circuit withstand time 10 µs

Applications

- High frequency motor controls
- SMPS and PFC in both hard switch and resonant topologies
- Motor drives

Description

This device utilizes the advanced Power MESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

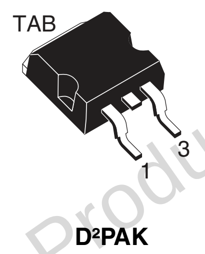


Figure 1. Internal schematic diagram

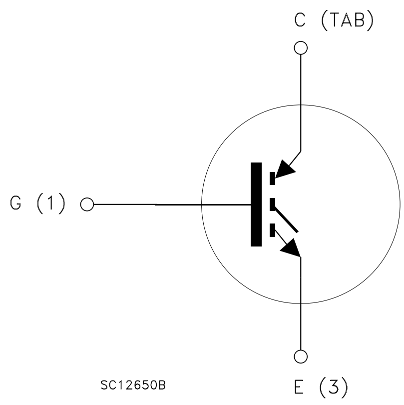


Table 1. Device summary

Part number	Marking	Package	Packaging
STGB10NC60KT4	GB10NC60K	D²PAK	Tape and reel

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage (V_{GE} = 0)	600	V
I_C (1)	Continuous collector current at T_C = 25°C	20	A
I_C (1)	Continuous collector current at T_C = 100°C	10	A
I_{CL} (2)	Turn-off latching current	30	A
I_{CP} (3)	Pulsed collector current	30	A
V_{GE}	Gate-emitter voltage	±20	V
P_{TOT}	Total dissipation at T_C = 25°C	65	W
T_{STG}	Storage temperature	– 55 to 150	°C
T_J	Operating junction temperature		
t_{SCW}	Short-circuit withstand time (V_{CE} = 0.5 V_{CES}, T_J = 125 °C, R_G = 10 Ω, V_{GE} = 12 V)	10	µs

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. V_{clamp} = 80 % V_{CES}, V_{GE} = 15 V, R_G = 10 Ω, T_J = 150 °C
3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance junction-case	1.9	°C/W
R_{thJA}	Thermal resistance junction-ambient	62.5	°C/W

2 Electrical characteristics

T_J = 25 °C unless otherwise specified.

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage (V_{GE}= 0)	I_C= 1mA	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	V_{GE}= 15V, I_C= 5A V_{GE}= 15V, I_C= 5A, T_J=125°C		2.2 1.8	2.5	V V
$V_{GE(th)}$	Gate threshold voltage	V_{CE}= V_{GE}, I_C= 250 µA	4.5		6.5	V
I_{CES}	Collector cut-off current (V_{GE} = 0)	V_{CE} = 600 V V_{CE} = 600 V, T_J = 125 °C			150 1	µA mA
I_{GES}	Gate-emitter leakage current (V_{CE} = 0)	V_{GE}= ± 20 V			±100	nA
g_{fs} (1)	Forward transconductance	V_{CE} = 15 V, I_C = 5A		15		S

1. Pulse test: pulse duration < 300 µs, duty cycle < 2 %.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies} C_{oes} C_{res}	Input capacitance Output capacitance Reverse transfer capacitance	V_{CE} = 25V, f = 1MHz, V_{GE} = 0		380 46 8.5		pF pF pF
Q_g Q_{ge} Q_{gc}	Total gate charge Gate-emitter charge Gate-collector charge	V_{CE} = 390V, I_C = 5A, V_{GE} = 15V, *(see Figure 17)*		19 5 9		nC nC nC

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390V, I_C = 5A R_G= 10Ω, V_{GE}= 15V, *(see Figure 18)*		17 6 655		ns ns A/µs
$t_{d(on)}$ t_r $(di/dt)_{on}$	Turn-on delay time Current rise time Turn-on current slope	V_{CC} = 390V, I_C = 5A R_G= 10Ω, V_{GE}= 15V, Tj=125°C *(see Figure 18)*		16.5 6.5 575		ns ns A/µs
$t_r(V_{off})$ $t_d(_{off})$ t_f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390V, I_C = 5A, R_{GE} = 10Ω, V_{GE} = 15V, *(see Figure 18)*		33 72 82		ns ns ns
$t_r(V_{off})$ $t_d(_{off})$ t_f	Off voltage rise time Turn-off delay time Current fall time	V_{cc} = 390V, I_C = 5A, R_{GE}=10Ω, V_{GE} =15V, Tj=125°C *(see Figure 18)*		60 106 136		ns ns ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min	Typ	Max	Unit
E_{on} (1) E_{off} (2) E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390V, I_C = 5A R_G= 10Ω, V_{GE}=15V, *(see Figure 18)*		55 85 140		µJ µJ µJ
E_{on} (1) E_{off} (2) E_{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390V, I_C = 5A R_G= 10Ω, V_{GE}= 15V, Tj= 125°C *(see Figure 18)*		87 162 249		µJ µJ µJ

1. Eon is the tun-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)
2. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

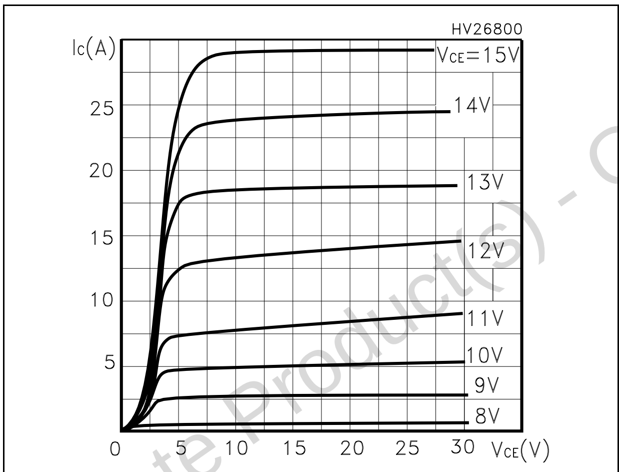


Figure 3. Transfer characteristics

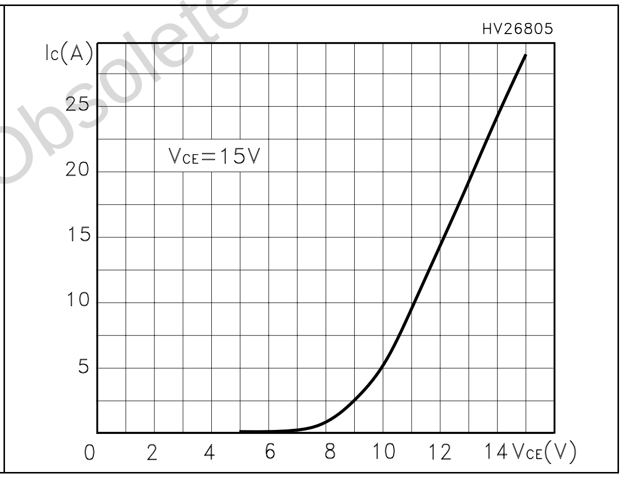


Figure 4. Transconductance

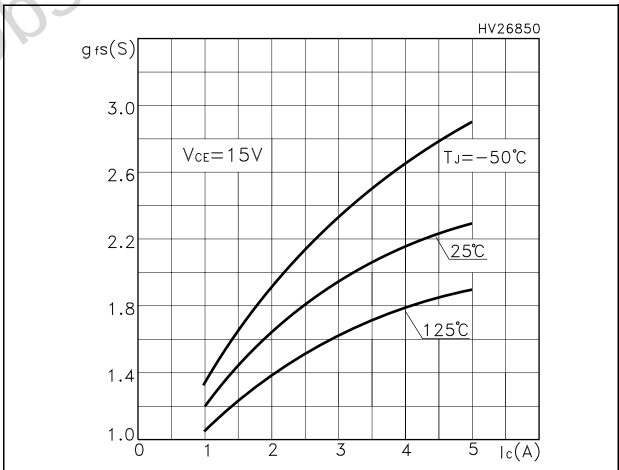


Figure 5. Collector-emitter on voltage vs temperature

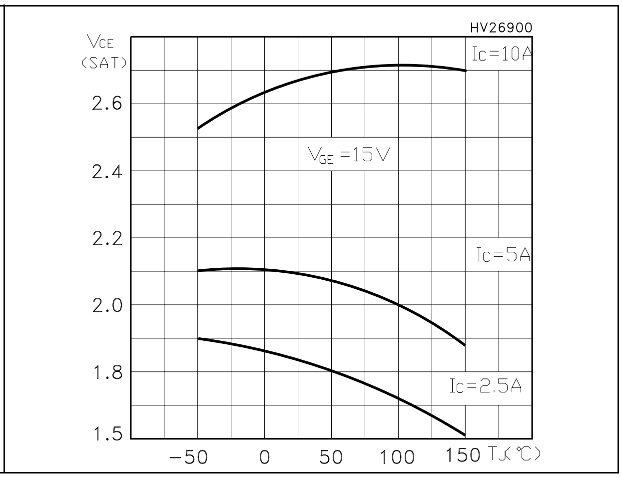


Figure 6. Gate charge vs. gate-source voltage

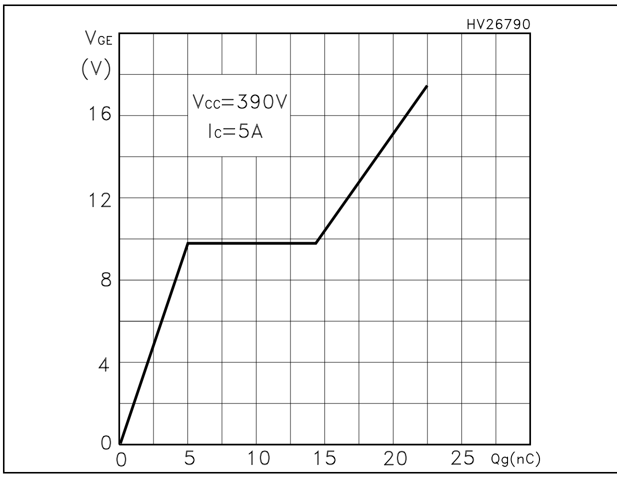


Figure 7. Capacitance variations

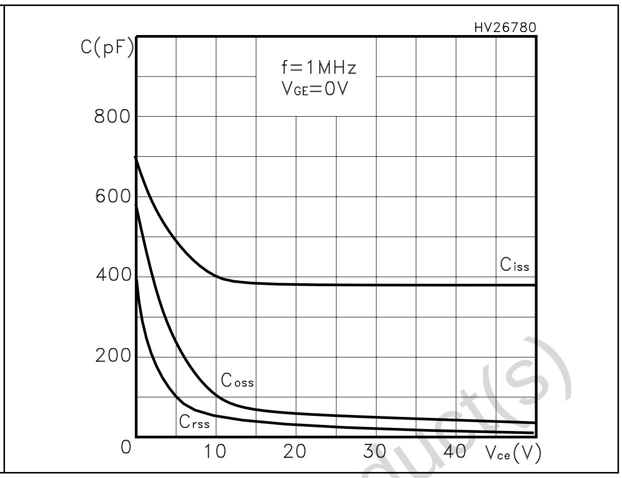


Figure 8. Normalized gate threshold voltage vs. temperature

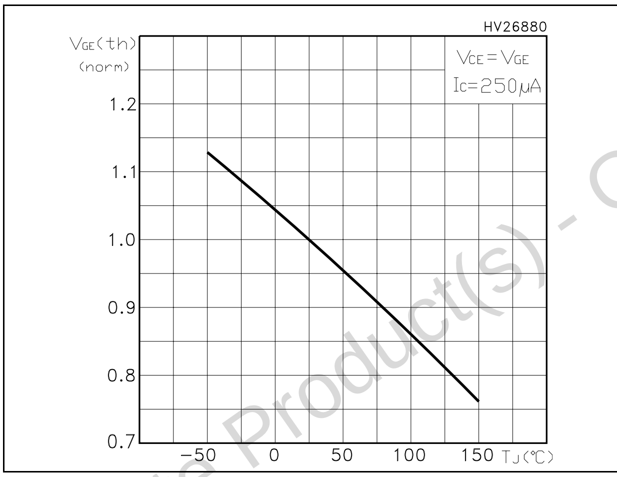


Figure 9. Collector-emitter on voltage vs collector current

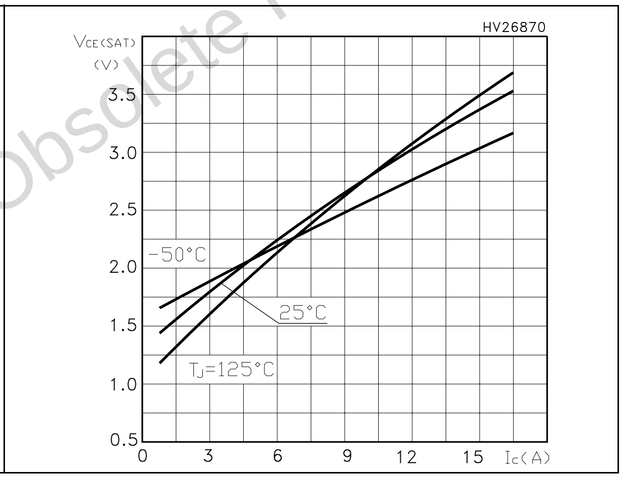


Figure 10. Normalized breakdown voltage vs temperature

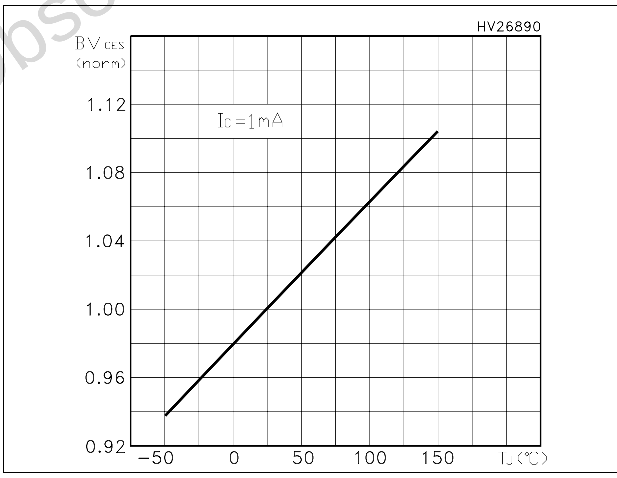


Figure 11. Switching losses vs temperature

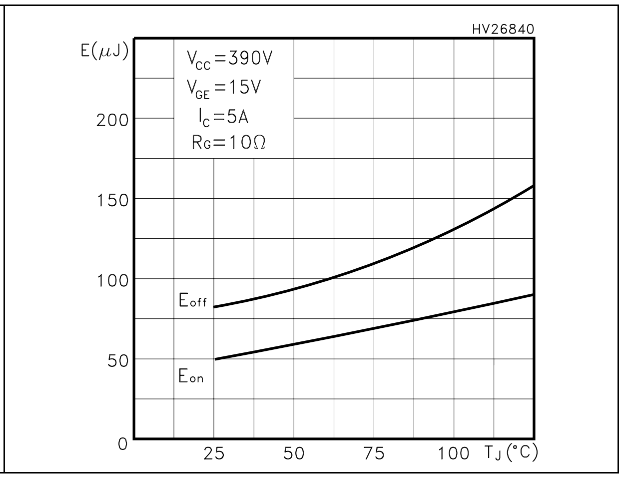


Figure 12. Switching losses vs. gate resistance

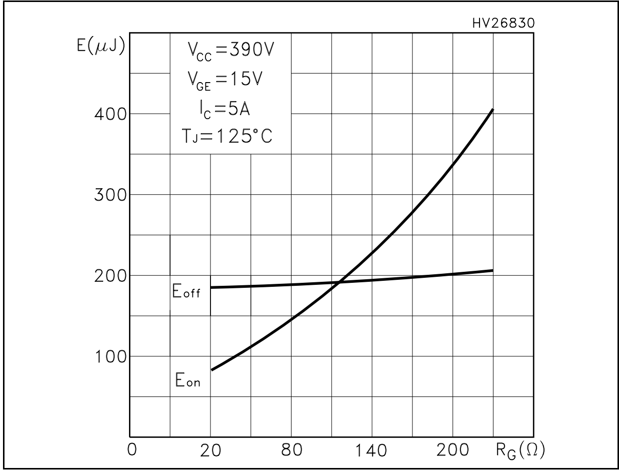


Figure 13. Switching losses vs collector current

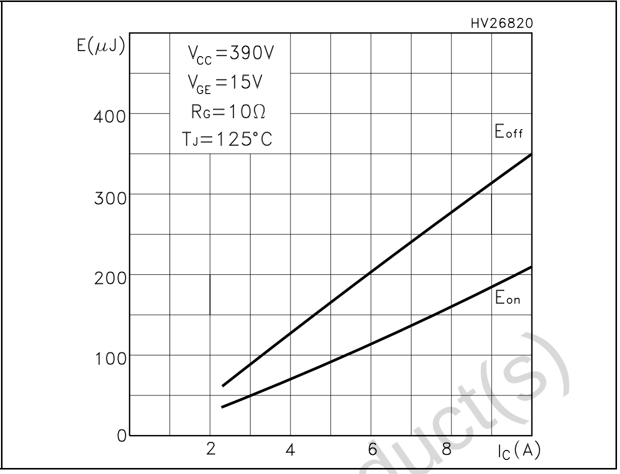


Figure 14. Thermal impedance

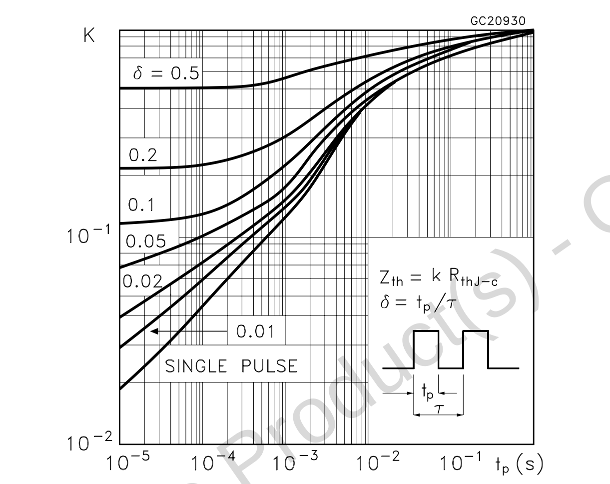
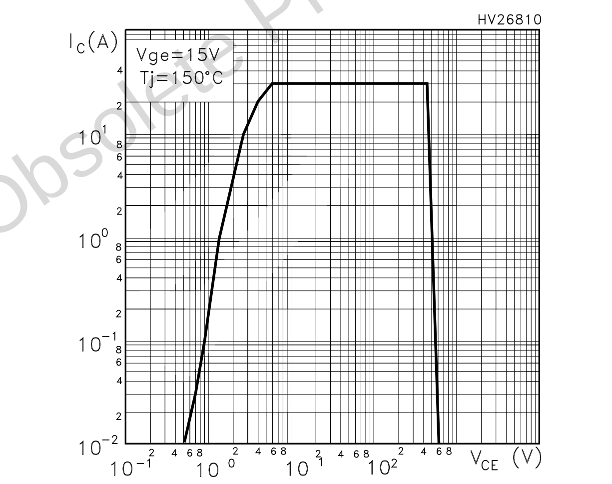


Figure 15. Turn-off SOA



3 Test circuits

Figure 16. Test circuit for inductive load switching

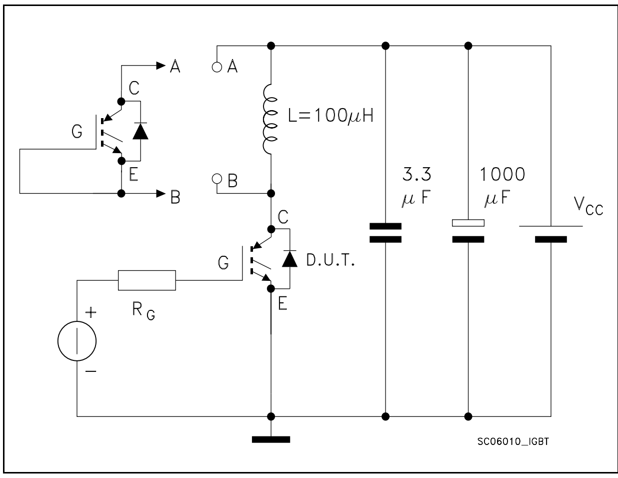


Figure 17. Gate charge test circuit

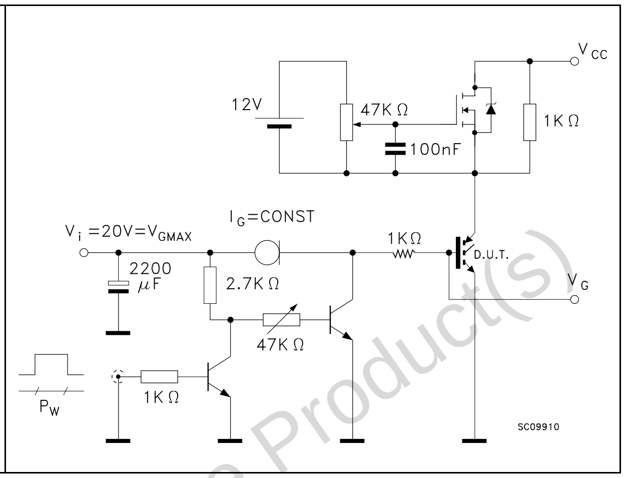
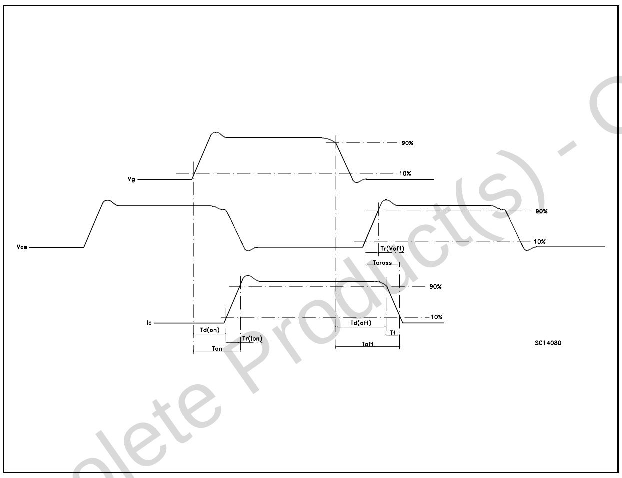


Figure 18. Switching waveform



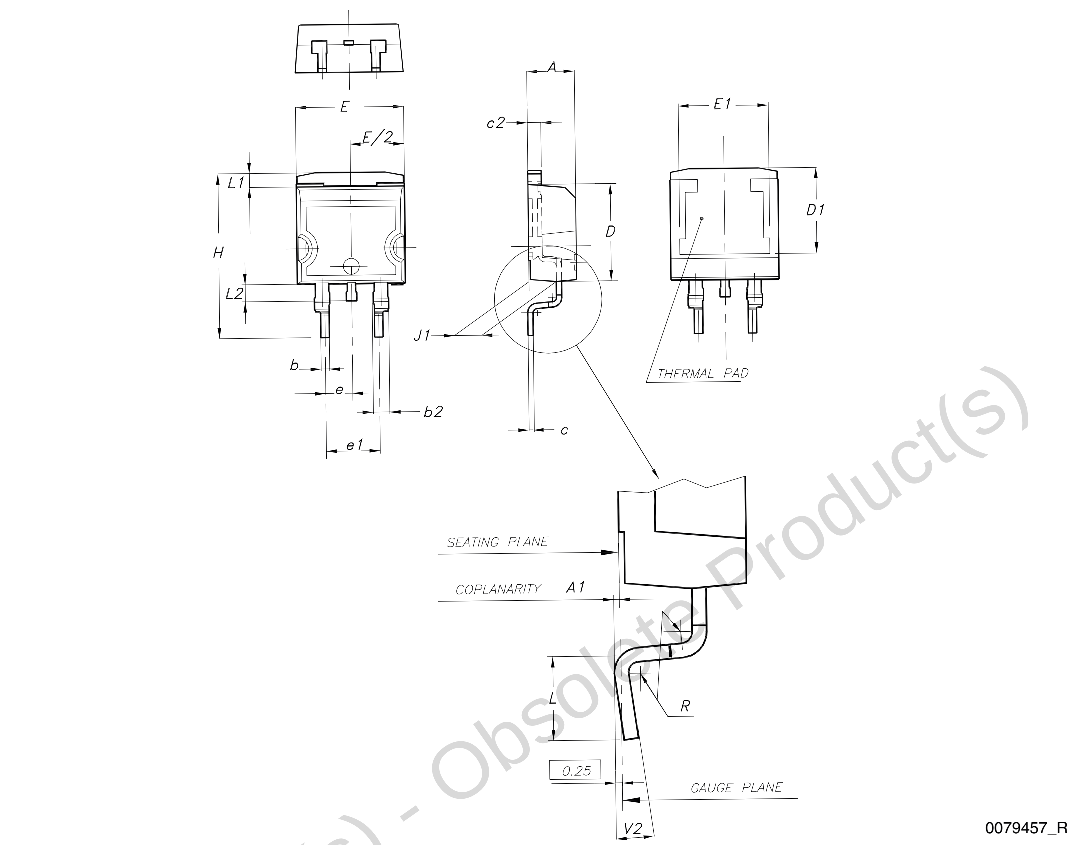
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Table 8. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 19. D²PAK (TO-263) drawing



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
21-Nov-2005	1	New release
06-Dic-2005	2	Inserted row on *Table 2: Absolute maximum ratings*
08-Feb-2007	3	Description has been updated
24-Feb-2011	4	Updated package mechanical data *Table 8. on page 8* and *Figure 19. on page 9*